

L Number	Hits	Search Text	DB	Time stamp
1	21	("4292093") or ("4942058") or ("5024968") or ("5352291") or ("5372836") or ("5424244") or ("5529630") or ("5593497") or ("5843225") or ("5842833").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 15:36
2	2	("5405804").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 15:36
-	2978	((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 11:18
-	2937	laser with crystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 10:07
-	1421	(laser with crystallization) and laser with anneal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 11:17
-	1379	((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 10:59
-	96	((((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and (preheat\$3 (pre adj heat\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 11:00
-	52	(((((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and clean\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 14:34
-	5	(((((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and clean\$4) and @ad<=19951025	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 11:35
-	2	("6348369").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 11:36
-	3	("4180618" "4851363" "5064779").PN.	USPAT	2003/01/03 13:30
-	25	4180618.URPN.	USPAT	2003/01/03 13:32
-	6	5344796.URPN.	USPAT	2003/01/03 13:56
-	9	("3998980" "4222814" "5242707" "5337207" "5344796" "5434102" "5587343" "5757061" "5834803").PN.	USPAT	2003/01/03 13:59
-	3	("4180618" "4851363" "5064779").PN.	USPAT	2003/01/03 14:09
-	25	4180618.URPN.	USPAT	2003/01/03 14:09
-	6	("4019169" "4180618" "4643950" "4732801" "4795679" "4847157").PN.	USPAT	2003/01/03 14:10
-	16	5108843.URPN.	USPAT	2003/01/03 14:10
-	52	(((((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and clean\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 14:35

-	334	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 15:16
-	249	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and oxygen and nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 14:43
-	264	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and (oxygen "o.sub.2") and (nitrogen "n.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 14:44
-	37	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and (oxygen "o.sub.2") and (nitrogen "n.sub.2")) and @ad<=19951025	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 14:44
-	52	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and (preheat\$3 (pre adj heat\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 15:17
-	0	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and ((preheat\$3 (pre adj heat\$3)) with (oxygen "o.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 15:18
-	45	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and ((preheat\$3 (pre adj heat\$3)) and (oxygen "o.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 15:20
-	4	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and ((preheat\$3 (pre adj heat\$3)) and (oxygen "o.sub.2")) and @ad<=19951025	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 15:18
-	270	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and ((heat\$3) and (oxygen "o.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 15:20
-	62	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and ((heat\$3) with (oxygen "o.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 15:20
-	10	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and clean\$4)) and ((heat\$3) with (oxygen "o.sub.2")) and @ad<=19951025	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 15:21
-	4493	laser with nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 10:28
-	2978	((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 10:10

2978	((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/FOR.200) or (438/FOR.269) or (438/FOR.334) or (117/8) or (117/9) or (117/10)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 10:10
73	(laser with nitrogen) and (((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/FOR.200) or (438/FOR.269) or (438/FOR.334) or (117/8) or (117/9) or (117/10)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 10:11
23	((laser with nitrogen) and (((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/FOR.200) or (438/FOR.269) or (438/FOR.334) or (117/8) or (117/9) or (117/10)).CCLS.)) and @ad<=19951025	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 10:12
1320	((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 10:32
847	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 11:46
258	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and laser) and anneal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 11:18
29	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and oxidation with nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 10:47
14	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and oxidation with nitrogen) and @ad<=19951025	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 11:45
48	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and laser with air	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 11:47
18	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and laser with air) and @ad<=19951025	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/06 11:47
118	(laser with crystallization) and laser with air	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 11:18
16	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and (laser with air)) and anneal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 11:19
4	(((((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and (laser with air)) and anneal) and @ad<=19951025	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/07 11:19